HBS802 THRU HBS810

Voltage Range - 200 to 1000 Volts Current - 8.0 Ampere

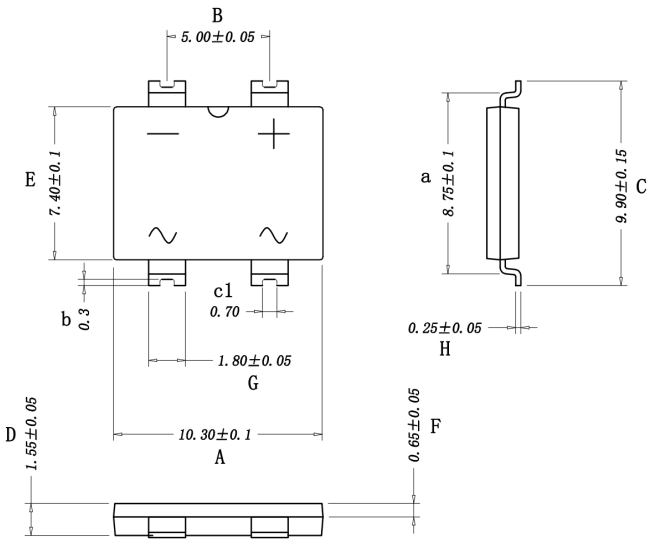
SINGLE PHASE GLASS PASSIVATED BRIDGE RECTIFIERS

Features

- Surface mount bridge, small package;
- Ideal for printed circuit boards;
- Glass passivated chip junction;
- High forward current capability up to 8.0A;
- High surge current capability;
- High heat dissipation capability;
- Low profile package;
- Low forward voltage drop;
- Plastic package has Underwrites Laboratory Flammability Classification 94V-0;

HBS

RoHS COMPLIANT



Dimensions in inches and (millimeters)

Mechanical Data

Case : JEDEC HBS Molded plastic body
Mounting Position: Any
High temperature soldering guaranteed: Solder Reflow 260℃,10seconds
Polarity: As marked on body

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwisespecified.

Single phase half-wave 60Hz,resistive or inductive load,for capacitive load current derate by 20%.

Parameter Marking Code	SYMBOLS	MDD HBS802	MDD HBS804	MDD HBS806	MDD HBS808	MDD HBS810	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	200	400	600	800	1000	V
Maximum average forward rectified current at T_A=25°C	$I_{F(AV)}$	8.0					A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	200					A
Maximum instantaneous forward voltage drop per diode at 8A	V_F	1.10					V
Maximum DC reverse current at rated DC blocking voltage T_A=25°C T_A=125°C	I_R	5 100					μA
Typical capacitance （note1)	C_J	49					pF
Typical thermal resistance	$R_{\theta JA}$ $R_{\theta JC}$ $R_{\theta JL}$	70 11 14					°C/W
Operating junction and Storage Temperature Range	T_j,T_{STG}	-55 to +150					°C

Note1: Measured at 1.0MHz and applied reverse voltage of 5.0V DC;

Ratings And Characteristic Curves

(TA = 25℃ unless otherwise noted)

FIG.1 Derating Curve Output Rectified Current

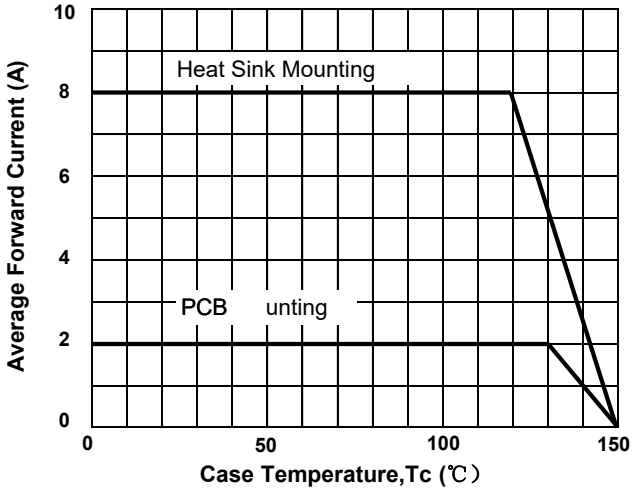


FIG.2 Typical Forward Characteristics per Diode

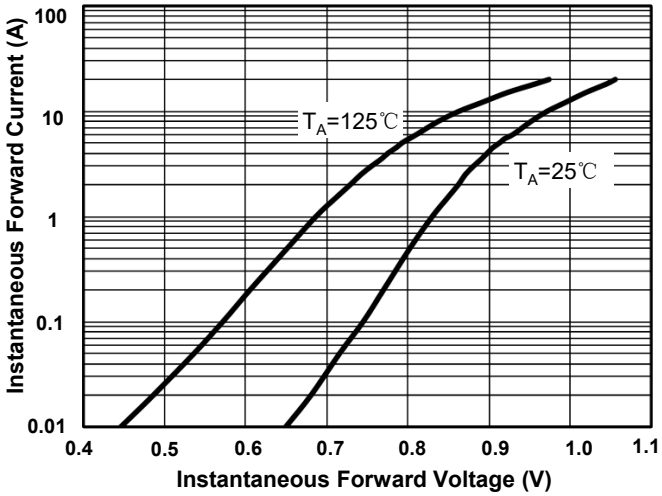


FIG.3 Maximum Non-Repetitive Peak Forward Surge Current per Diode

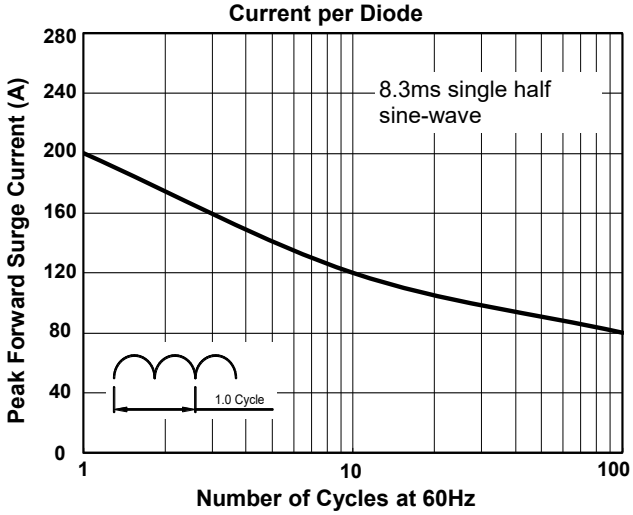


FIG.4 Typical Reverse Characteristics per Diode

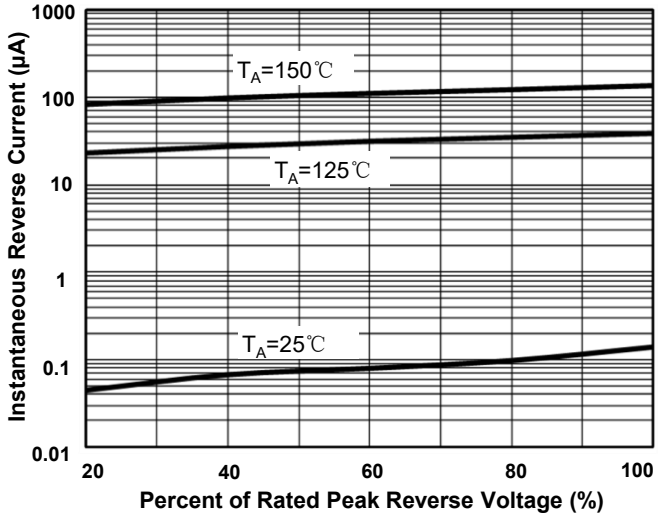
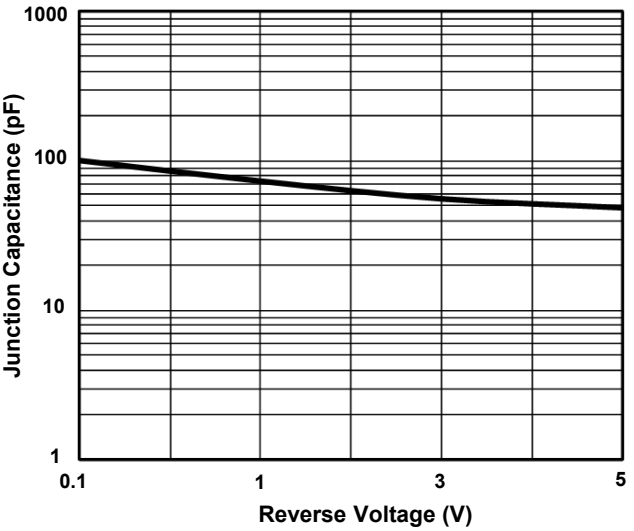


FIG.5 Typical Junction Capacitance per Diode



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